

High Efficiency Thyristor

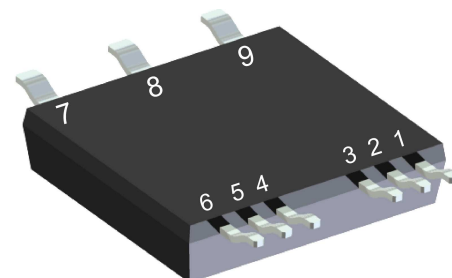
3~ Rectifier	
V_{RRM}	= 1200 V
I_{DAV}	= 90 A
I_{FSM}	= 350 A

SemiFast
 3~ Rectifier Bridge, half-controlled (high-side)

Part number

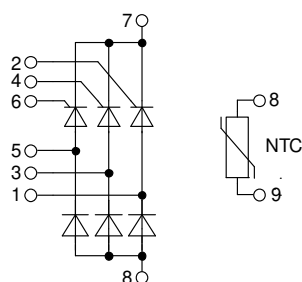
CLE90UH1200TLB

Marking on Product: CLE90UH1200TLB



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line and moderate frequencies
- Short turn-off time
- Planar passivated chip
- Long-term stability

Applications:

- Line rectifying 50/60 Hz
- Drives
- SMPS
- UPS

Package: SMPD

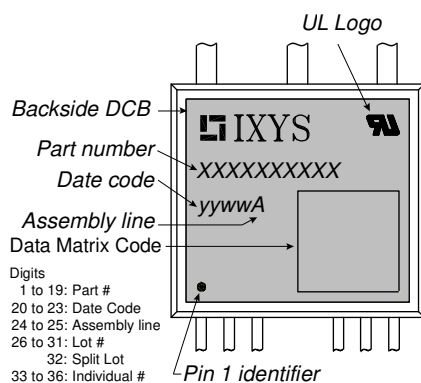
- Isolation Voltage: 3000 V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			10	μA
		$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$			2	mA
V_T	forward voltage drop	$I_T = 30\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.30	V
		$I_T = 90\text{ A}$				1.80	V
		$I_T = 30\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.28	V
		$I_T = 90\text{ A}$				1.95	V
I_{DAV}	bridge output current	$T_C = 90^{\circ}\text{C}$ 120° sine	$T_{VJ} = 150^{\circ}\text{C}$			90	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}\text{C}$			0.92	V
r_T	slope resistance					13	m Ω
R_{thJC}	thermal resistance junction to case					0.9	K/W
R_{thCH}	thermal resistance case to heatsink				0.40		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			140	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			350	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			380	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			300	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			320	A
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			615	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			600	A ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			450	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			425	A ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		13		pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 150^{\circ}\text{C}$			10	W
		$t_p = 300\text{ }\mu\text{s}$				5	W
P_{GAV}	average gate power dissipation					0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 90\text{ A}$				150	A/ μs
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 0.3\text{ A}/\mu\text{s};$ $I_G = 0.3\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 30\text{ A}$				500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}\text{C}$			500	V/ μs
		$R_{GK} = \infty$; method 1 (linear voltage rise)					
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1.4	V
			$T_{VJ} = -40^{\circ}\text{C}$			1.7	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			30	mA
			$T_{VJ} = -40^{\circ}\text{C}$			50	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}\text{C}$			0.2	V
I_{GD}	gate non-trigger current					1	mA
I_L	latching current	$t_p = 10\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$			90	mA
		$I_G = 0.3\text{ A}; di_G/dt = 0.3\text{ A}/\mu\text{s}$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$			60	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$			2	μs
		$I_G = 0.3\text{ A}; di_G/dt = 0.3\text{ A}/\mu\text{s}$					
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 30\text{ A}; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^{\circ}\text{C}$ $di/dt = 10\text{ A}/\mu\text{s}$ $dv/dt = 20\text{ V}/\mu\text{s}$ $t_p = 200\text{ }\mu\text{s}$			50		μs

Package SMPD				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				100	A
T _{VJ}	virtual junction temperature			-55		150	°C
T _{op}	operation temperature			-55		125	°C
T _{stg}	storage temperature			-55		150	°C
Weight					8.5		g
F _C	mounting force with clip			40		130	N
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal		1.6			mm
d _{Spb/Apb}		terminal to backside		4.0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA	3000			V
		t = 1 minute		2500			V



Part description

C = Thyristor (SCR)
 L = High Efficiency Thyristor
 E = Semifast (up to 1200V)
 90 = Current Rating [A]
 UH = 3~ Rectifier Bridge, half-controlled (high-side)
 1200 = Reverse Voltage [V]
 T = Thermistor \ Temperature sensor
 LB = SMPD-B

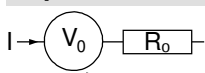
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CLE90UH1200TLB-TUB	CLE90UH1200TLB	Tube	20	517456
Alternative	CLE90UH1200TLB-TRR	CLE90UH1200TLB	Tape & Reel	200	517463

Temperature Sensor NTC

Symbol	Definition	Conditions	min.	typ.	max.	Unit
R_{25}	resistance	$T_{VJ} = 25^\circ$	4.75	5	5.25	k Ω
$B_{25/50}$	temperature coefficient			3375		K

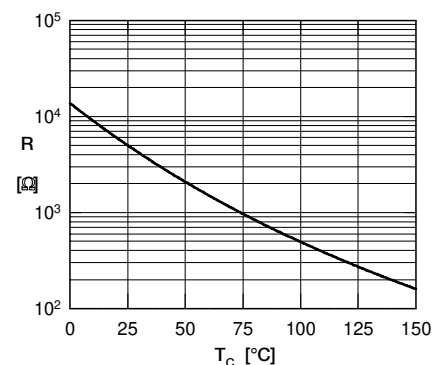
Equivalent Circuits for Simulation

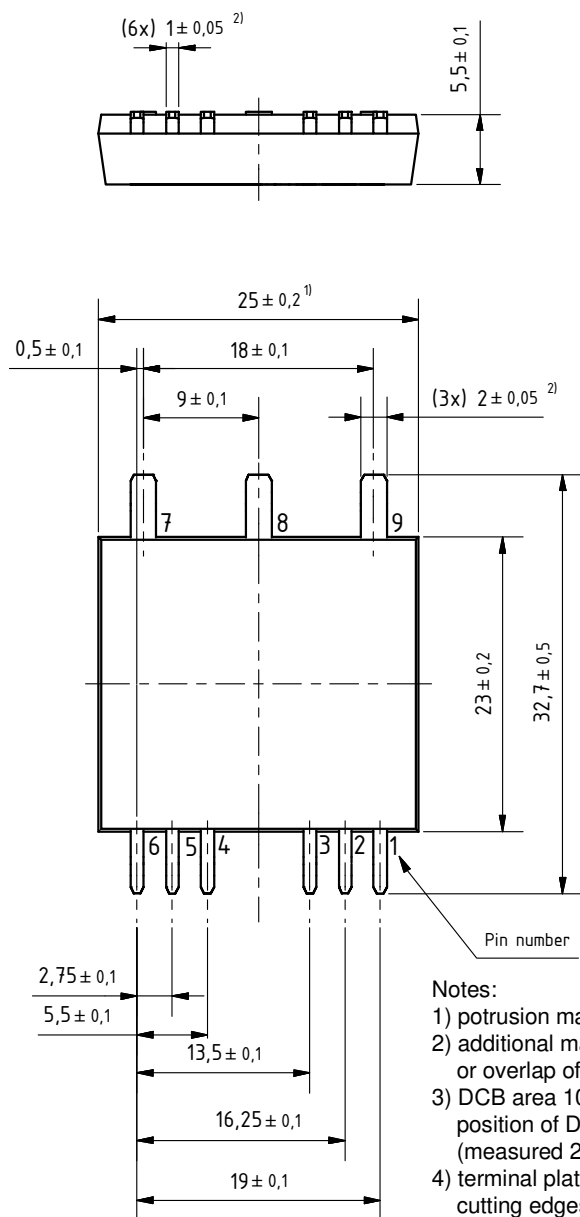
* on die level

 $T_{VJ} = 150^\circ\text{C}$


$V_{0\max}$ threshold voltage 0.92 V

$R_{0\max}$ slope resistance * 10.5 m Ω



Outlines SMPD
A (8 : 1)

Notes:

- 1) potrusion may add 0.2 mm max. on each side
- 2) additional max. 0.05 mm per side by punching misalignement or overlap of dam bar or bending compression
- 3) DCB area 10 to 50 μm convex;
position of DCB area in relation to plastic rim: $\pm 25 \mu\text{m}$ (measured 2 mm from Cu rim)
- 4) terminal plating: 0.2 - 1 μm Ni + 10 - 25 μm Sn (gal v.)
cutting edges may be partially free of plating

